

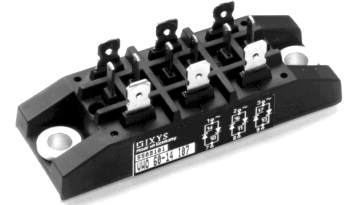
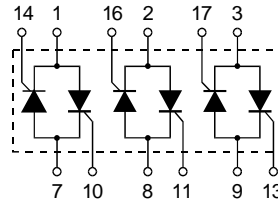
Three Phase AC Controller Modules

$$I_{RMS} = 3 \times 60 \text{ A}$$

$$V_{RRM} = 800-1600 \text{ V}$$

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
800	800	VWO 60-08io7
1200	1200	VWO 60-12io7
1400	1400	VWO 60-14io7
1600	1600	VWO 60-16io7



Symbol	Test Conditions	Maximum Ratings
I_{RMS}	$T_K = 85^\circ\text{C}$, 50 - 400 Hz (per phase)	60 A
I_{TRMS}	$T_{VJ} = T_{VJM}$	43 A
I_{TAVM}	$T_K = 85^\circ\text{C}$; (180° sine)	27 A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine 550 A t = 8.3 ms (60 Hz), sine 600 A
	$T_{VJ} = T_{VJM}$; $V_R = 0$	t = 10 ms (50 Hz), sine 500 A t = 8.3 ms (60 Hz), sine 550 A
I^2t	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine 1520 A ² s t = 8.3 ms (60 Hz), sine 1520 A ² s
	$T_{VJ} = T_{VJM}$; $V_R = 0$	t = 10 ms (50 Hz), sine 1250 A ² s t = 8.3 ms (60 Hz), sine 1250 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$; f = 50 Hz, t _p = 200 μs	repetitive, I _T = 25 A 150 A/μs
	$V_D = 2/3 V_{DRM}$; I _G = 0.45 A; di _G /dt = 0.45 A/μs	non repetitive, I _T = I _{TAVM} 500 A/μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM} 1000 V/μs
P_{GM}	$T_{VJ} = T_{VJM}$	t _p = 30 μs 10 W
	I _T = I _{TAVM}	t _p = 300 μs 5 W
P_{GAVM}		0.5 W
V_{RGM}		10 V
T_{VJ}		-40...+125 °C
T_{VJM}		125 °C
T_{stg}		-40...+125 °C
V_{ISOL}	50/60 Hz, RMS	t = 1 min 2500 V~
	I _{ISOL} ≤ 1 mA	t = 1 s 3000 V~
M_d	Mounting torque (M5) (10-32 UNF)	5 ± 15 % Nm
		44 ± 15 % lb.in.
Weight	typ.	110 g

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Package with metal base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- UL applied
- 1/4" fast-on power terminals

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- Light and temperature control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Light weight and compact

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤ 5 mA
V_T	$I_T = 45$ A; $T_{VJ} = 25^\circ\text{C}$	≤ 1.45 V
V_{T0}	For power-loss calculations only	0.85 V
r_T		11 m Ω
V_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤ 1.5 V ≤ 1.6 V
I_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤ 100 mA ≤ 200 mA
V_{GD} I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤ 0.2 V ≤ 5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10$ μs $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μs	≤ 450 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	≤ 200 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μs	≤ 2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20$ A, $t_p = 200$ μs ; $di/dt = -10$ A/ μs $V_R = 100$ V; $dv/dt = 15$ V/ μs ; $V_D = 2/3 V_{DRM}$	typ. 150 μs
R_{thJC}	per thyristor; sine 180°el per module	0.9 K/W 0.15 K/W
R_{thJK}	per thyristor; sine 180°el per module	1.1 K/W 0.183 K/W
d_S	Creeping distance on surface	16.1 mm
d_A	Creepage distance in air	6.0 mm
a	Max. allowable acceleration	50 m/s ²

Dimensions in mm (1 mm = 0.0394")
